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| L8 and (thin\$4 same (implant\$5 or dop\$4)) | 1009 |

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L10

Search History

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| <u>L10</u> | L8 and (thin\$4 same (implant\$5 or dop\$4)) | 1009 | <u>L10</u> |
| <u>L9</u> | L8 and implant\$5 | 1598 | <u>L9</u> |
| <u>L8</u> | L7 and (thin\$4 with (oxide or dielectric or insulat\$3)) | 1915 | <u>L8</u> |
| <u>L7</u> | (L4 or L5) and (HV or HVMOSFET or (high adj voltage) or (high adj breakdown)) | 3187 | <u>L7</u> |
| <u>L6</u> | L4 or L5 and (HV or HVMOSFET or (high adj voltage) or (high adj breakdown)) | 10136 | <u>L6</u> |
| <u>L5</u> | 257/288,314-316,368,409.ccls. | 7132 | <u>L5</u> |
| <u>L4</u> | 438/197,201,211,229-232,257,266,301,303,305-307.ccls. | 8309 | <u>L4</u> |
| <u>L3</u> | L2 and (((thickness with (oxide or insulat\$4)) same (thin or thinner or thinnest))) | 1030 | <u>L3</u> |
| <u>L2</u> | L1 and (((deposit\$4 or cover\$4 or screen\$4 or mask\$3) with (drain or source))) | 3894 | <u>L2</u> |

L1 (transistor or MOSFET) with (HV or (high adj voltage) or (high adj
breakdown))

34751 L1

END OF SEARCH HISTORY